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U.S. PTO

GAO 2785

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of)
ELIYAHOU HARARI, ROBERT D.)
NORMAN and SANJAY MEHROTRA)
Serial No.: 08/771,708)
Filed: December 20, 1996)
For: FLASH EEPROM SYSTEM)

Group Art Unit: 2785

San Francisco, California

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L. docket
13/1998

Assistant Commissioner for Patents
Washington, D.C. 20231

By Express Mail #: EM215669675US
Dated: February 2, 1998

THIRD PRELIMINARY AMENDMENT TRANSMITTAL

Sir:

Transmitted herewith is a Third Preliminary Amendment in
the captioned application, of which no additional fee is required.

Respectfully submitted,

Dated: February 2, 1998

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Atty. Docket: HARI.006USE

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THIRD PRELIMINARY AMENDMENT

Sir:

Please further amend certain of the claims of the above-identified patent application, prior to a substantive examination thereof, as follows:

163. (Twice Amended) A method of operating an EEPROM system having memory cells that individually include an electrically floating gate carrying a charge level that is alterable in response to appropriate voltage conditions being applied to the cell in order to set a variable threshold level thereof into a range that is determinable by reading the cell [to be in one of at least two defined threshold level regions], said method comprising:

applying said appropriate voltage conditions in parallel to a plurality of said memory cells [in parallel], thereby to alter the charge levels on the floating gates of said plurality of memory cells,

determining the threshold level [regions] ranges [of] in which individual ones of said plurality of memory cells lie, and

terminating said application of appropriate voltage conditions to individual ones of said plurality of memory cells